

N-CHANNEL SILICON POWER MOSFET

FAP-2S Series

■ Features

High speed switching
Low on-resistance
No secondary breakdown
Low driving power
Avalanche-proof

■ Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

■ Maximum ratings and characteristic Absolute maximum ratings

● (T_c=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V _{DS}	800	V
Continuous drain current	I _D	±7	A
Pulsed drain current	I _D (puls)	±28	A
Gate-source voltage	V _{GS}	±35	V
Repetitive or non-repetitive	IAR*2	7	A
Maximum Avalanche Energy	EAS*1	145	mJ
Max. power dissipation	P _D	80	W
Operating and storage	T _{ch}	+150	°C
temperature range	T _{stg}	-55 to +150	°C

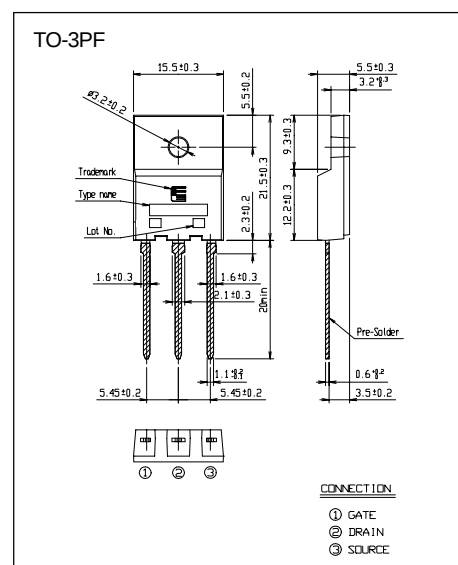
*1 L=5.4mH, V_{CC}=80V *2 T_{ch}≤150°C● Electrical characteristics (T_c =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =1mA V _{GS} =0V	800			V
Gate threshold voltage	V _{GS(th)}	I _D =1mA V _{DS} =V _{GS}	3.5	4.0	4.5	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =800V V _{GS} =0V		10	500	μA
		T _{ch} =25°C				
		V _{GS} =0V		0.2	1.0	mA
		T _{ch} =125°C				
Gate-source leakage current	I _{GSS}	V _{GS} =±35V V _{DS} =0V		10	100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =3.5A V _{GS} =10V		1.62	2.0	Ω
Forward transconductance	g _{fs}	I _D =3.5A V _{DS} =25V	2.0	4.0		S
Input capacitance	C _{iss}	V _{DS} =25V		900	1350	pF
Output capacitance	C _{oss}	V _{GS} =0V		130	200	
Reverse transfer capacitance	C _{rss}	f=1MHz		70	110	
Turn-on time t _{on}	td(on)	V _{CC} =600V I _D =7A		25	40	ns
	t _r	V _{GS} =10V		90	140	
Turn-off time t _{off}	td(off)	R _{GS} =10Ω		80	120	
	t _f			50	80	
Avalanche capability	I _{AV}	L=100μH T _{ch} =25°C	7			A
Diode forward on-voltage	V _{SD}	I _F =2I _{DR} V _{GS} =0V T _{ch} =25°C		1.0	1.5	V
Reverse recovery time	t _{rr}	I _F =I _{DR} V _{GS} =0V		900		ns
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		10.0		μC

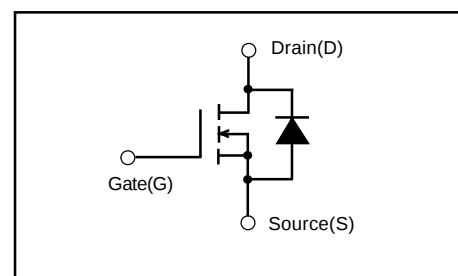
● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			1.56	°C/W
	R _{th(ch-a)}	channel to ambient			30.0	°C/W

■ Outline Drawings



■ Equivalent circuit schematic



Characteristics

